

# 18NM80-VB TO220 Datasheet

## N-Channel 800V (D-S)Super Junction Power MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V) at T <sub>J</sub> max.	800	
R <sub>DS(on)</sub> at 25 °C (Ω)	V <sub>GS</sub> = 10 V	0.24
Q <sub>g</sub> max. (nC)	140	
Q <sub>gs</sub> (nC)	21	
Q <sub>gd</sub> (nC)	37	
Configuration	Single	

**FEATURES**

- Low figure-of-merit (FOM) R<sub>on</sub> x Q<sub>g</sub>
- Low input capacitance (C<sub>iss</sub>)
- Reduced switching and conduction losses
- Ultra low gate charge (Q<sub>g</sub>)
- Avalanche energy rated (UIS)

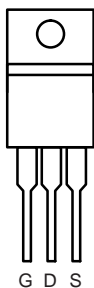


**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

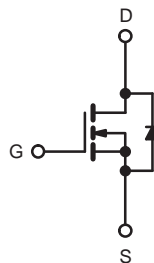
**APPLICATIONS**

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial

TO-220AB



Top View




N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	800	V	
Gate-Source Voltage		V <sub>GS</sub>	± 30		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 10 V	I <sub>D</sub>	T <sub>C</sub> = 25 °C	20	A
			T <sub>C</sub> = 100 °C	15	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	76		
Linear Derating Factor			2.2	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>		E <sub>AS</sub>	691	mJ	
Maximum Power Dissipation		P <sub>D</sub>	250	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Drain-Source Voltage Slope	T <sub>J</sub> = 125 °C	dV/dt	37	V/ns	
Reverse Diode dV/dt <sup>d</sup>			18		
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s		300	°C	

**Notes**

- Repetitive rating; pulse width limited by maximum junction temperature.
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 28.2 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 7 A.
- 1.6 mm from case.
- I<sub>SD</sub> ≤ I<sub>D</sub>, dI/dt = 100 A/μs, starting T<sub>J</sub> = 25 °C.

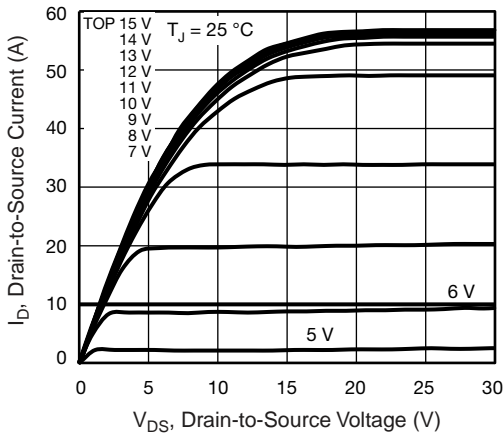
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.55	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		800	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.74	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}$	-	0.24	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 8\text{ V}, I_D = 5\text{ A}$		-	9.2	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	3315	-	pF
Output Capacitance	$C_{oss}$			-	148	-	
Reverse Transfer Capacitance	$C_{rss}$			-	4	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	89	-	pF
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	307	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}, V_{DS} = 520\text{ V}$	-	73	110	nC
Gate-Source Charge	$Q_{gs}$			-	15	-	
Gate-Drain Charge	$Q_{gd}$			-	32	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	22	45	ns
Rise Time	$t_r$			-	33	66	
Turn-Off Delay Time	$t_{d(off)}$			-	73	110	
Fall Time	$t_f$			-	38	76	
Gate Input Resistance	$R_g$			$f = 1\text{ MHz}, \text{ open drain}$		-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	20	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	76	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 11\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	400	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	5.9	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	20	-	A

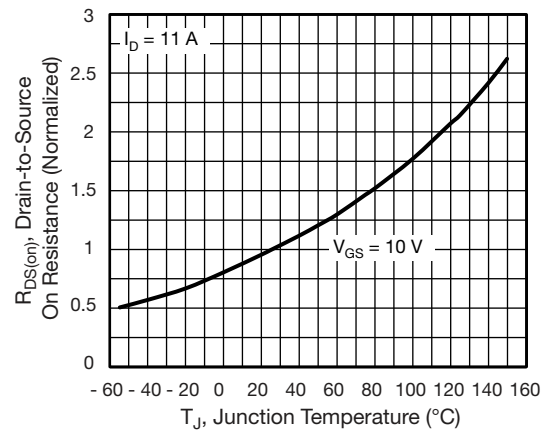
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

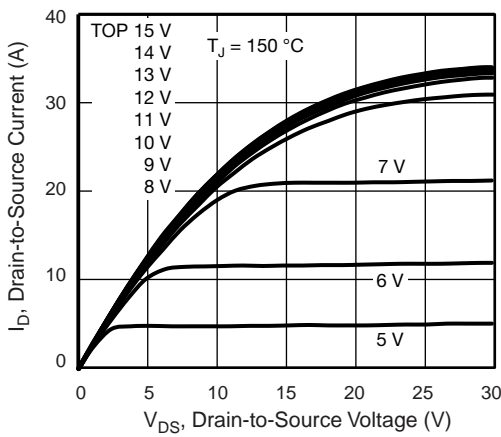
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



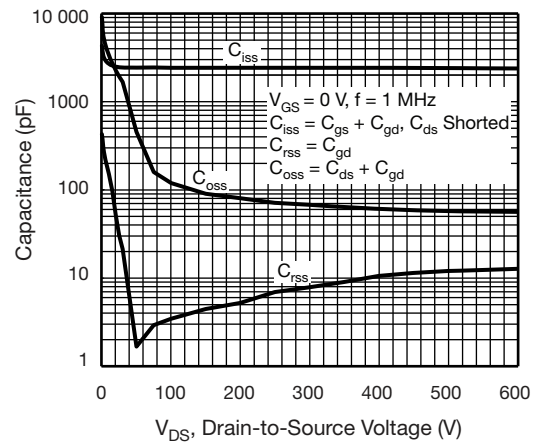
**Fig. 1 - Typical Output Characteristics**



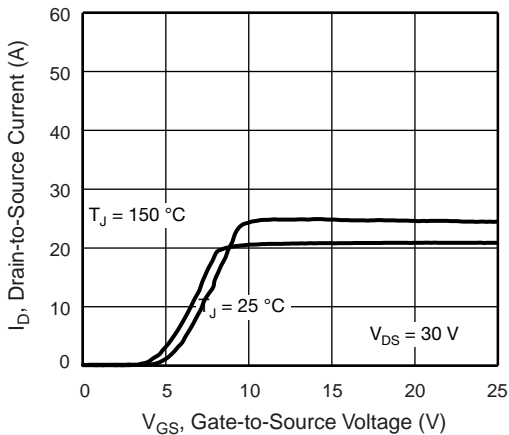
**Fig. 4 - Normalized On-Resistance vs. Temperature**



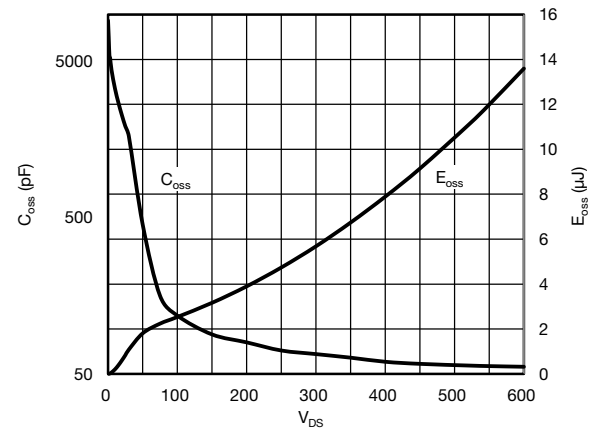
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**



Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

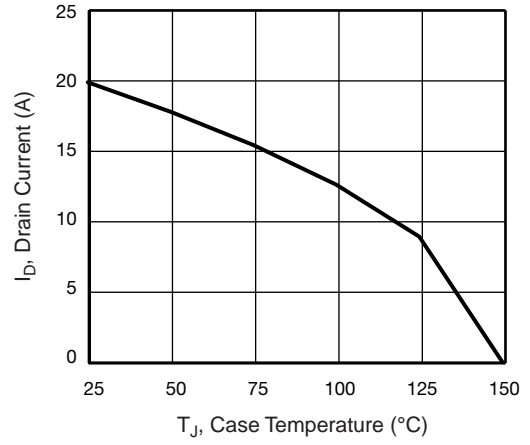


Fig. 10 - Maximum Drain Current vs. Case Temperature

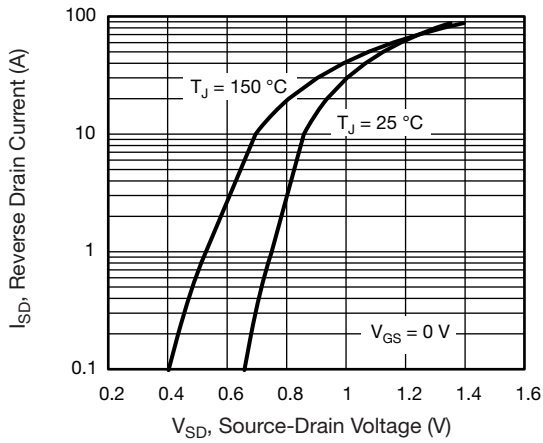


Fig. 8 - Typical Source-Drain Diode Forward Voltage

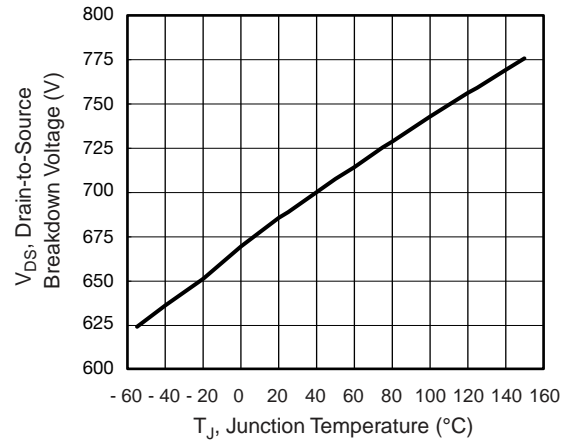


Fig. 11 - Temperature vs. Drain-to-Source Voltage

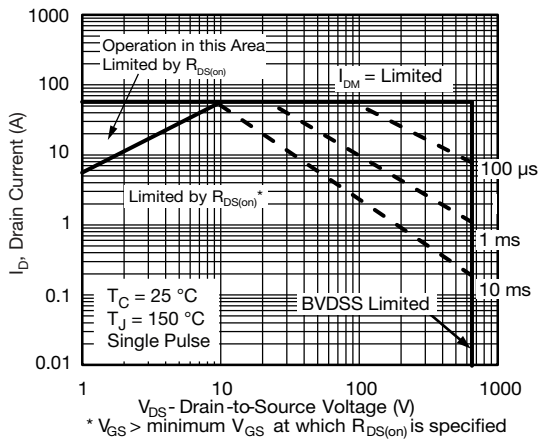


Fig. 9 - Maximum Safe Operating Area

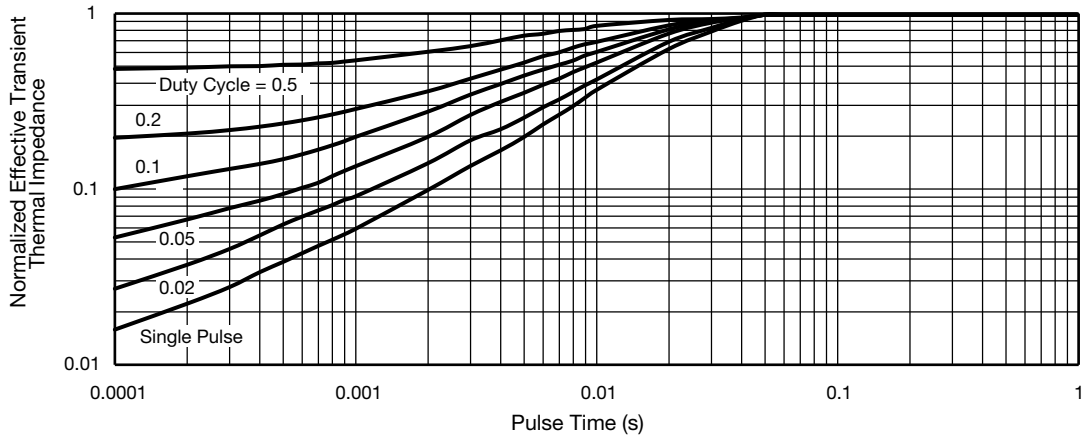


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

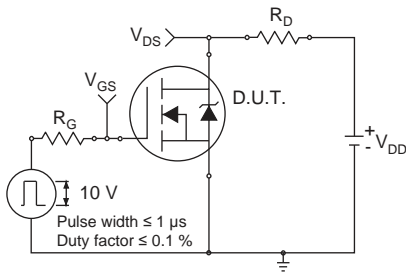


Fig. 13 - Switching Time Test Circuit

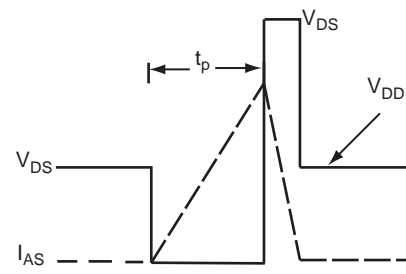


Fig. 16 - Unclamped Inductive Waveforms

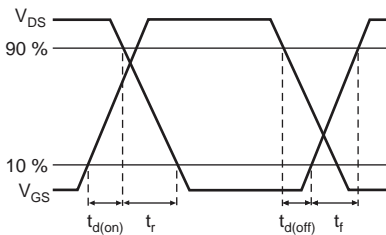


Fig. 14 - Switching Time Waveforms

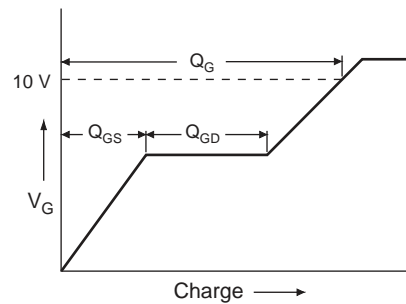


Fig. 17 - Basic Gate Charge Waveform

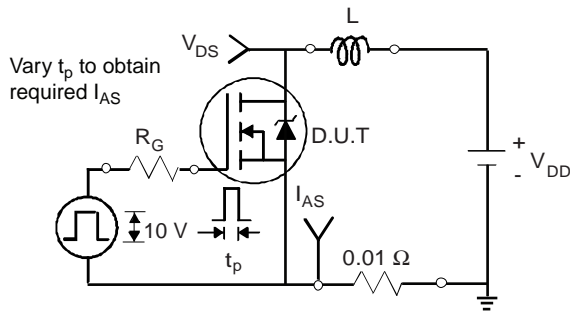


Fig. 15 - Unclamped Inductive Test Circuit

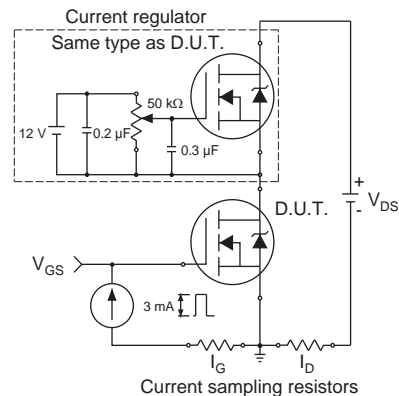
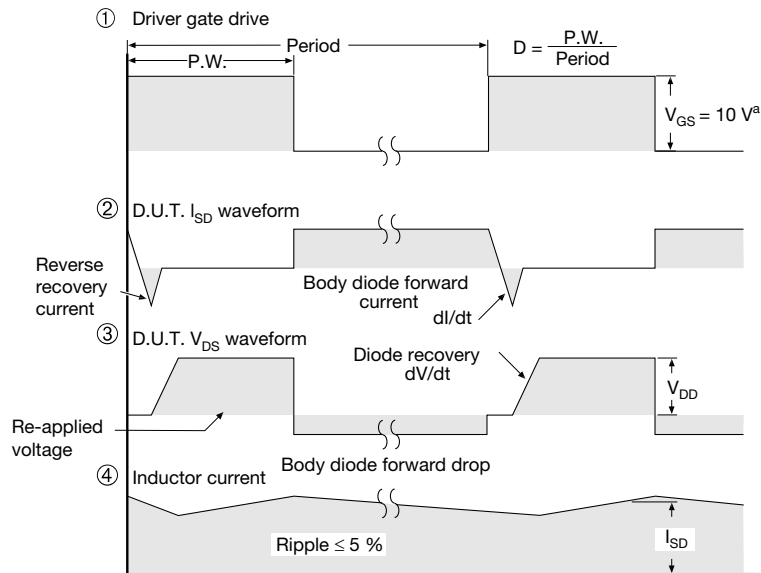
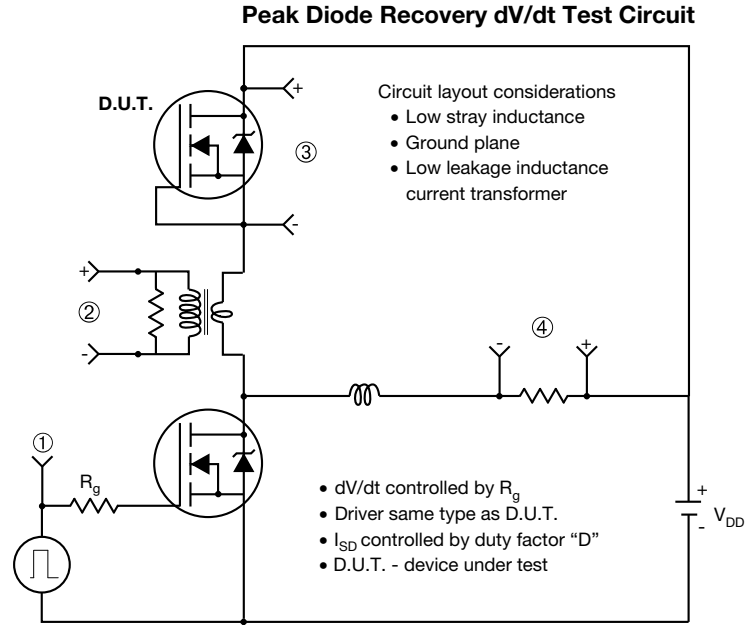


Fig. 18 - Gate Charge Test Circuit

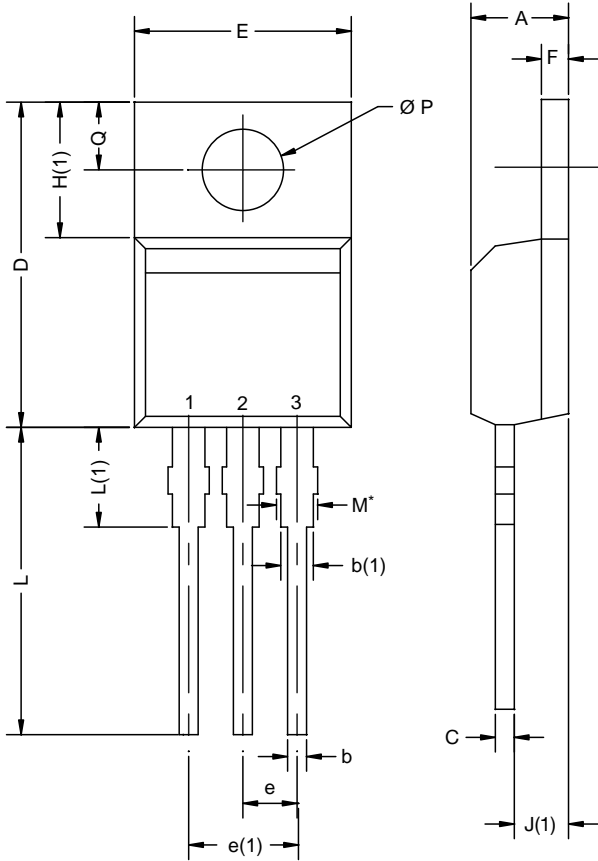


**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 19 - For N-Channel**

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

Notes

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM

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